

Research Project Valleytronics in Strain-Engineered Graphene

## Third-party funded project

Project title Valleytronics in Strain-Engineered Graphene Principal Investigator(s) Schönenberger, Christian ; Co-Investigator(s) Calame, Michel ; Organisation / Research unit Departement Physik / Experimentalphysik Nanoelektronik (Schönenberger) Department Project Website www.nanoscience.ch Project start 01.01.2016 Probable end 31.12.2019 Status Completed This project is part of the Swiss Nanoscience Institute (SNI)

We aim to explore strain induced effects in the electrical properties of clean ballistic graphene. Graphene can be strained to >20% yielding gigantic pseudo-magnetic fields which act on the valley-degree of freedom. This opens the door to valleytronics with observable electro-optical effects in ballistic graphene, such as angle-dependent refraction at a p-n interface that dependy on the valley degree of freedom.

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